GTMi, Inc.

Solution, Service, Performance, and Commitment

- Your Trusted Partner

Product Data Sheet

Model: MA0912-250

GaN/SiC High Efficiency Transistor

GaN Transistor Product Features

MA0912-250 is designed for application of drop-in replacement of MAGX-000912-250L00. This is an internally pre-matched GaN on SiC HEMT, common source, class AB that capable of providing 250 Watts of pulsed RF output power at 128µS pulse width, 10% duty factor across the 960 to 1215 MHz band. This thermally enhanced transistor is designed for Broadband Avionic Data Link applications. It utilizes gold metallization and eutectic die attach to provide highest reliability and superior ruggedness.

- *High Power* > 250*W*
- *High Efficiency* >55%
- Drop-in Replacement MAGX-000912-250L00

Market Application

- Avionics ATC
- Secondary Radar for IFF & Mode-S Avionics
- TCAS, JTIDS, DME, and TACAN
- Communication, and Data Links
- General Purpose Driver Stage

Case Outline

The following illustrations show the case outline of model MA0912-250



.800"x.385"x.162" (include lid)

Case 1: Case Outline T6

Absolute Maximum Ratings

Description	Test Condition	Max	Units
Maximum Power Dissipation	Transistor Dissipation at 25°C	500	W
MVI	Drain Source Voltage (V_{DSS})	150	V
Maximum Voltage and Current	Gate Source Voltage (V_{GS})	-8 to 0	V
MT	Storage Temperature	-55 to 125	°C
Maximum Temperature	Operating Junction Temperature	200	°C

RF Specifications, T=25° C

Symbol	Description	Test Condition	Min	Typical	Max	Units
Pin	Input Power	Pout=250W Freq=960, 1090, 1215 MHz		2.5	5	Watts
Gp	Power Gain	Pout=250W Freq=960, 1090, 1215 MHz	17	19.5		dB
n_d	Drain Efficiency	Pout=250W Freq=960, 1090, 1215 MHz	52	59		%
IRL	Input Return Loss	Pout=250W Freq=960, 1090, 1215 MHz		-10	-7	dB
VSWR-T	Mismatch Tolerance	Po=250W Freq=960MHz, 128μS, 10%			5:1	
θ_{jc}	Thermal Resistance	128µS, 10% Condition		0.25		°C/W

[•] Bias Condition: Vdd = 50V, Idq = 80mA (Vgs = -2 to -4V typical)

DC Characteristics, T=25° C

Symbol	Description	Test Condition	Min	Typical	Max	Units
$I_{D(off)}$	Drain Leakage Current	V_{GS} = -8V, V_{DD} = 150V			10	mA
$I_{G(off)}$	Gate Leakage Current	V_{GS} = -8V, V_{DD} = 0V			4	mA

Product Classification

EAR-99

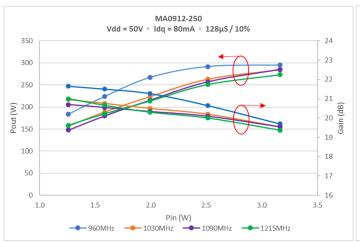
Typical Performance Data

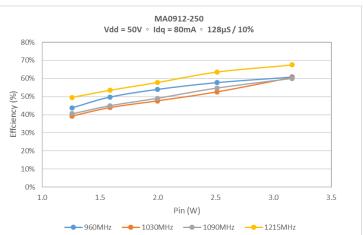
Pulse Format $128\mu S - 10\%$ - Po=250W

Freq (MHz)	Pin (W)	Pout (W)	ld (A)	Eff (%)	RL (dB)	Droop (dB)	Gain (dB)
960	1.78	250	1.00	54	-9.0	.40	21.5
1030	2.24	250	1.03	53	-7.4	.35	20.5
1090	2.45	250	0.98	56	-7.0	.30	20.1
1215	2.63	250	0.87	63	-9.2	.20	19.8

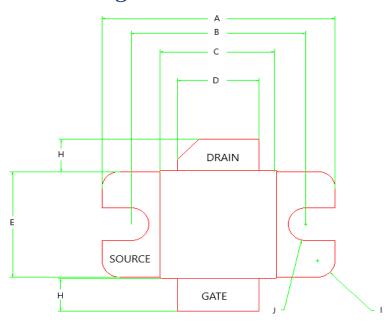
Pulse Format $128\mu S - 10\%$ - Pin=3.16W

Freq (MHz)	Pin (W)	Pout (W)	ld (A)	Eff (%)	RL (dB)	Droop (dB)	Gain (dB)
960	3.16	296	1.05	61	-9.0	.40	19.7
1030	3.16	284	1.03	60	-7.4	.35	19.5
1090	3.16	285	1.03	60	-7.0	.30	19.6
1215	3.16	274	0.89	68	-9.2	.20	19.4





Package Dimensions





Dimension	Min (mil)	Min (mm)	Max (mil)	Max (mm)
Α	800	20.32	806	20.47
В	600	15.24	606	15.39
С	400	10.16	406	10.31
D	280	7.11	286	7.26
E	385	9.78	400	10.16
F	005	.127	006	.152
G	040	1.02	041	1.04
Н	102	2.59	122	3.10
I	R = 025	.635	-	-
J	R = 060	1.52	-	-
K	162	4.11	168	4.26
L	062	1.57	064	1.63

Test Circuit Information

Test Circuit is equivalent to MAGX-000912-250L00 Test Fixture

(Contact GTMi for Details)

The information contained in the document is PROPRIETARY AND CONFIDENTIAL information of GTMi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of GTMi If the recipient of this document has entered into a disclosure agreement with GTMi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of GTMi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by GTMi in writing signed by an officer of GTMi.

GTMi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with life-support or other mission-critical equipment or applications. GTMi assumes no liability whatsoever, and GTMi disclaims any express or implied warranty, relating to sale and/or use of GTMi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. The product is subject to other terms and conditions which can be located on the Web at http://www.microsemi.com/legal/tnc.asp.

Revision History

Revision Level / Date	Para. Affected	Description
Rev 2 / 05-10-2020	-	Initial Preliminary Release
	_	